

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method for manufacturing an electro-optical substrate including a composite base plate obtained by joining a support plate to a semiconductor plate having semiconductor layers, comprising:

forming a light-shielding layer, having a predetermined pattern, over a support plate;

forming an insulating layer over the light-shielding layer having the predetermined pattern;

providing a semiconductor layer over the insulating layer;

partially oxidizing the semiconductor layer to form an oxide layer; and

completely removing the oxide layer, the oxide layer having a thickness smaller than that of the insulating layer.

2. (Previously Presented) The method for manufacturing an electro-optical substrate according to Claim 1, further comprising:

patterning the semiconductor layer; and

oxidizing parts of the semiconductor layer having a predetermined pattern to form the oxide layer,

the patterning step and oxidizing step being performed after the semiconductor layer-providing step.

3. (Currently Amended) ~~The method~~ A method for manufacturing an electro-optical substrate ~~according to Claim 1, including a composite base plate obtained by joining a support plate to a semiconductor plate having semiconductor layers, comprising:~~

forming a light-shielding layer, having a predetermined pattern, over a support plate;

forming an insulating layer over the light-shielding layer having the predetermined pattern;

providing a semiconductor layer over the insulating layer;

partially oxidizing the semiconductor layer to form an oxide layer; and

removing the oxide layer, the oxide layer having a thickness smaller than that of the insulating layer,

the method further comprising:

oxidizing parts of the semiconductor layer to form gate oxide layers, and
the semiconductor layer-oxidizing step being performed after the oxide layer-removing step.

4. (Previously Presented) The method for manufacturing an electro-optical substrate according to Claim 1, the oxide layer having a thickness smaller than that of parts of the insulating layer disposed in areas above which the semiconductor layer is not placed, and which are disposed on the light-shielding layer.

5. (Original) The method for manufacturing an electro-optical substrate according to Claim 1, further comprising:

forming a silicon nitride layer or silicon oxide nitride layer between the light-shielding layer and the insulating layer.

6. (Previously Presented) The method for manufacturing an electro-optical substrate according to Claim 1, the semiconductor layer-providing step including a sub-step of joining a single-crystal semiconductor plate including the semiconductor layer to a support plate including the insulating layer.

7. (Original) The method for manufacturing an electro-optical substrate according to Claim 1, the light-shielding layer containing a high-melting metal or a silicide containing a high-melting metal.
8. (Original) A method for manufacturing an electro-optical apparatus including a semiconductor element, comprising manufacturing an electro-optical substrate including the semiconductor element by the manufacturing method according to Claim 1.
9. Cancelled.